IN THE SPECIFICATION:

Please amend the specification as follows:

At page 6, kindly amend the paragraph at lines 10-14 as follows:

A1

Reference is made to the figures to illustrate selected embodiments and preferred modes of carrying out the invention. It is to be understood that the invention is not hereby limited to those aspects depicted in the figures. As a matter of lexicographic convenience, the terms "underlayer," "organic underlayer," "anti-reflective coat," and "ARC" are used interchangeably. As a matter of lexicographic convenience, the terms "PR" and "photoresist" are used interchangeably.

At page 8, kindly amend the paragraph at lines 3-6 as follows:

A2

Suitable organic, polymeric, planarizing underlayers for the resist of the present invention include epoxies, diamond-like carbon, and novolac. The underlayer comprises the elements C, H, and O. In a preferred embodiment of the invention the tuned polymer is a thermally linked dyed phenolic polymer. Other crosslinkable polymers known to those skilled in the art can also be used as the underlayer. The polymers may be synthesized from monomers selected from the group consisting of acrylate, methacrylate, hydroxystyrene optionally substituted with C_{1-6}-alkyl, C_{5-20} cyclic olefin monomers, and combinations thereof, the polymer having acid-cleavable moieties bound thereto, wherein all such moieties are silylethoxy groups optionally substituted on the ethoxy portion thereof with C_{1-6}-alkyl, phenyl, or benzyl.

At page 8, kindly amend the paragraph at lines 12-25 as follows:

In the next step of the process, the film stack **8**, comprising the top imaging layer **7** and underlayer **6** is imagewise exposed to radiation. Suitable radiation includes electromagnetic radiation or electron beam radiation, preferably ultraviolet radiation suitably at a wavelength of about 157-365 nm (157/193/248/254/365/and hard and soft x-ray and euv), more preferably 193 or 248 nm. Preferably, the radiation is substantially monochromatic radiation. Suitable radiation sources include mercury, mercury/xenon, and xenon lamps. The preferred radiation source is an excimer, *e.g.* ArF, KrF, or F_2. At longer wavelengths (e.g., 365 nm) a sensitizer may be added to the top, imaging layer **7** to enhance absorption of the radiation. Conveniently, due to the enhanced radiation sensitivity of the top layer of the resist film, the top layer of the film has a fast photospeed and is fully exposed with less than about 100 mJ/cm^2 of radiation, more preferably less than about 50 mJ/cm^2. The radiation is absorbed by the radiation-sensitive acid generator or sensitizing agent to generate free acid which causes cleavage of the silicon-containing, acid-cleavable group and formation of the corresponding carboxylic acid or phenol.

A3

At page 9, kindly amend the paragraph at lines 6-10 as follows:

The last step of the process involves transferring of the developed image in the top layer **7**, through the underlayer **6**, and stopping on substrate **1** by known, ~~oxygen~~ reactive ion etching techniques. Reactive ion etching is achieved using a plasma comprised of O, H, F, Cl, and neutral species. ~~Oxygen~~ reactive ion etching techniques are well known in the art and equipment to etch film is commercially available. The developed film has high aspect ratio, high etch resistance, enhanced resolution, and straight wall profiles.

A4